

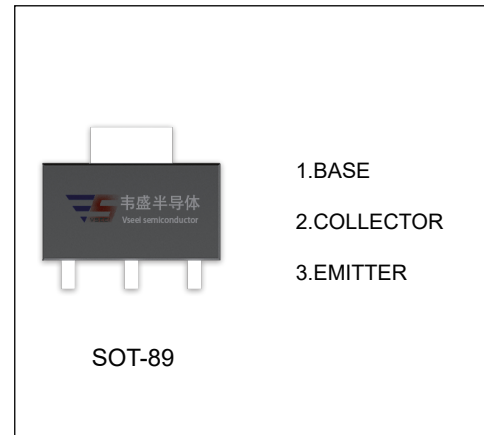
2SD2150 TRANSISTOR (NPN)

FEATURES

- Excellent current-to-gain characteristics
- Low collector saturation voltage $V_{CE(sat)}$
 $V_{CE(sat)}=0.5V(max)$ for $I_C/I_B=2A/0.1A$

MAXIMUM RATINGS ($T_a=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	20	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	3	A
P_C	Collector Power Dissipation	500	mW
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~150	$^\circ C$



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 50\mu A, I_E = 0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1mA, I_B = 0$	20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 50\mu A, I_C = 0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB} = 30V, I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5V, I_C = 0$			0.1	μA
DC current gain	h_{FE}^*	$V_{CE} = 2V, I_C = 100mA$	180		560	
Collector-emitter saturation voltage	$V_{CE(sat)}^*$	$I_C = 2A, I_B = 100mA$			0.5	V
Transition frequency	f_T^*	$V_{CE} = 2V, I_C = 500mA$ $f = 100MHz$		290		MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$		25		pF

*Pulse test: $t_p \leq 300\mu s, \delta \leq 0.02$.

CLASSIFICATION OF h_{FE}

Rank	R	S
Range	180-390	270-560
Marking	CFR	CFS

